MPSA14 is a Preferred Device

Darlington Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|-----------------------------------|-------------|-------------|
| Collector - Emitter Voltage | V _{CES} | 30 | Vdc |
| Collector - Base Voltage | V _{CBO} | 30 | Vdc |
| Emitter-Base Voltage | V _{EBO} | 10 | Vdc |
| Collector Current – Continuous | IC | 500 | mAdc |
| Total Device Dissipation @ T _A = 25°C Derate above 25°C | P _D | 625 5.0 | mW mW/°C |
| Total Device Dissipation @ T _C = 25°C Derate above 25°C | P _D | 1.5 12 | W mW/°C |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -55 to +150 | °C |

THERMAL CHARACTERISTICS

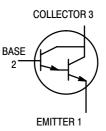
| Characteristic | Symbol | Max | Unit |
|---|-----------------|------|-------|
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 200 | °C/mW |
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 83.3 | °C/mW |

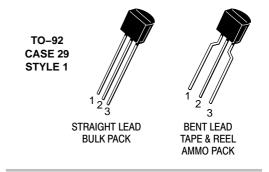
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



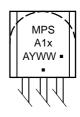
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MARKING DIAGRAM



x = 3 or 4

A = Assembly Location

Y = Year

WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

1

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

| Characteristic | | Symbol | Min | Max | Unit |
|--|--------------------------------------|----------------------|-------------------------------------|------------------|------|
| OFF CHARACTERISTICS | | | | | |
| Collector – Emitter Breakdown Voltage ($I_C = 100 \mu Adc, I_B = 0$) | | $V_{(BR)CES}$ | 30 | - | Vdc |
| Collector Cutoff Current (V _{CB} = 30 Vdc, I _E = 0) | | I _{CBO} | - | 100 | nAdc |
| Emitter Cutoff Current (V _{EB} = 10 Vdc, I _C = 0) | | I _{EBO} | - | 100 | nAdc |
| ON CHARACTERISTICS (Note 1) | | | | | |
| DC Current Gain ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 100 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$) | MPSA13 MPSA14 MPSA13 MPSA14 | h _{FE} | 5,000 10,000 10,000 20,000 | - - - - | - |
| Collector – Emitter Saturation Voltage (I _C = 100 mAdc, I _B = 0.1 mAdc) | | V _{CE(sat)} | - | 1.5 | Vdc |
| Base – Emitter On Voltage (I _C = 100 mAdc, V _{CE} = 5.0 Vdc) | | V _{BE(on)} | - | 2.0 | Vdc |
| SMALL-SIGNAL CHARACTERISTICS | | | | | |
| Current–Gain – Bandwidth Product (Note 2) (I _C = 10 mAdc, V _{CE} = 5.0 Vdc, f = 100 MHz) | | f _T | 125 | _ | MHz |

^{1.} Pulse Test: Pulse Width $\leq 300 \,\mu\text{s}$; Duty Cycle $\leq 2.0\%$.

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|-------------|--------------------|-----------------------|
| MPSA13 | TO-92 | 5000 Units / Bulk |
| MPSA13G | TO-92 (Pb-Free) | 5000 Units / Bulk |
| MPSA13RLRA | TO-92 | 2000 / Tape & Reel |
| MPSA13RLRAG | TO-92 (Pb-Free) | 2000 / Tape & Reel |
| MPSA13RLRMG | TO-92 (Pb-Free) | 2000 / Ammo Pack |
| MPSA13RLRPG | TO-92 (Pb-Free) | 2000 / Ammo Pack |
| MPSA13ZL1G | TO-92 (Pb-Free) | 2000 / Ammo Pack |
| MPSA14G | TO-92 (Pb-Free) | 5000 Units / Bulk |
| MPSA14RLRAG | TO-92 (Pb-Free) | 2000 / Tape & Reel |
| MPSA14RLRPG | TO-92 (Pb-Free) | 2000 / Ammo Pack |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{2.} $f_T = |h_{fe}| \cdot f_{test}$.

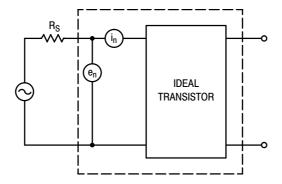


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$

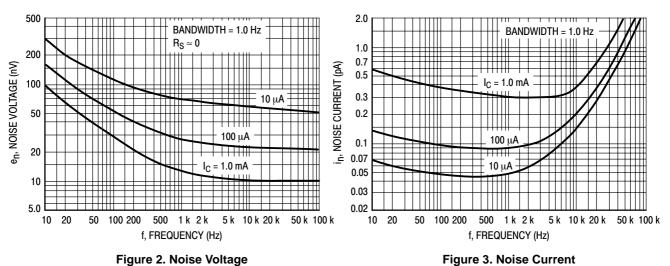


Figure 2. Noise Voltage

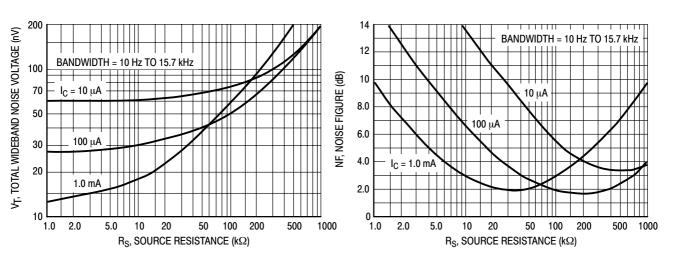


Figure 4. Total Wideband Noise Voltage

Figure 5. Wideband Noise Figure

SMALL-SIGNAL CHARACTERISTICS

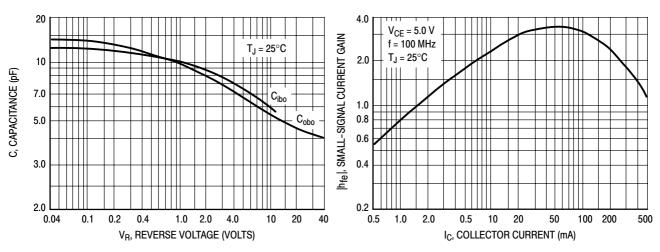


Figure 6. Capacitance

Figure 7. High Frequency Current Gain

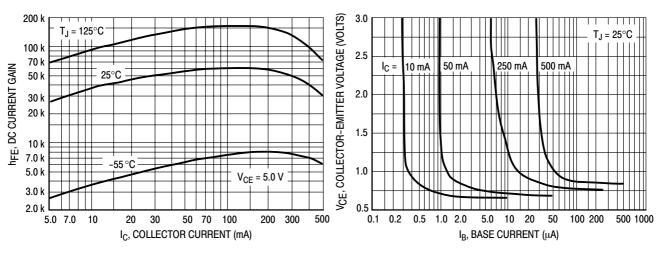


Figure 8. DC Current Gain

Figure 9. Collector Saturation Region

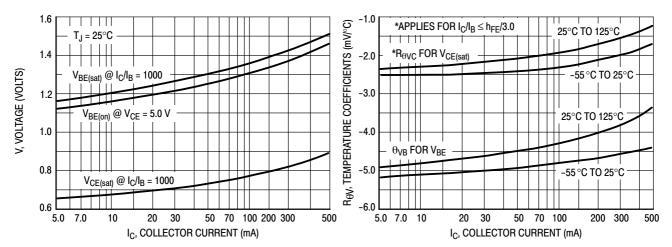


Figure 10. "On" Voltages

Figure 11. Temperature Coefficients

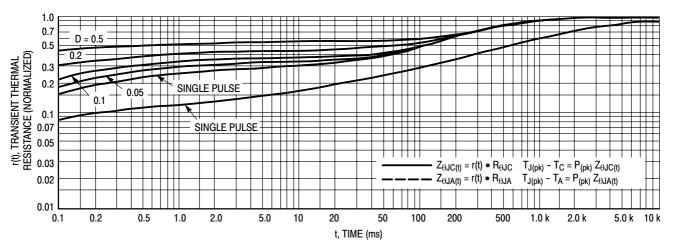


Figure 12. Thermal Response

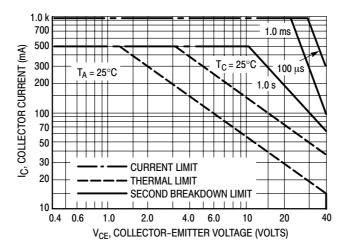
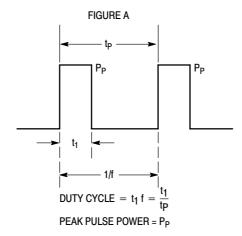
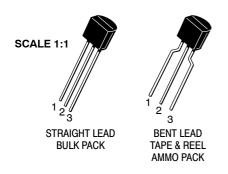


Figure 13. Active Region Safe Operating Area

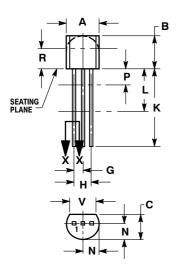


Design Note: Use of Transient Thermal Resistance Data



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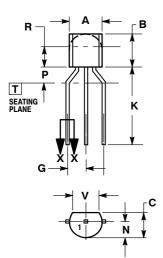


STRAIGHT LEAD **BULK PACK**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- DIMENSIONING AND IDECRANGING FER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

| | INC | HES | MILLIN | IETERS |
|-----|-------|-------|--------|--------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.175 | 0.205 | 4.45 | 5.20 |
| В | 0.170 | 0.210 | 4.32 | 5.33 |
| С | 0.125 | 0.165 | 3.18 | 4.19 |
| D | 0.016 | 0.021 | 0.407 | 0.533 |
| G | 0.045 | 0.055 | 1.15 | 1.39 |
| Н | 0.095 | 0.105 | 2.42 | 2.66 |
| J | 0.015 | 0.020 | 0.39 | 0.50 |
| K | 0.500 | | 12.70 | |
| L | 0.250 | | 6.35 | |
| N | 0.080 | 0.105 | 2.04 | 2.66 |
| P | | 0.100 | | 2.54 |
| R | 0.115 | | 2.93 | |
| ٧ | 0.135 | | 3.43 | |



BENT LEAD TAPE & REEL AMMO PACK



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

| | MILLIMETERS | | | | | |
|-----|-------------|------|--|--|--|--|
| DIM | MIN | MAX | | | | |
| Α | 4.45 | 5.20 | | | | |
| В | 4.32 | 5.33 | | | | |
| С | 3.18 | 4.19 | | | | |
| D | 0.40 | 0.54 | | | | |
| G | 2.40 | 2.80 | | | | |
| J | 0.39 | 0.50 | | | | |
| K | 12.70 | | | | | |
| N | 2.04 | 2.66 | | | | |
| P | 1.50 | 4.00 | | | | |
| R | 2.93 | | | | | |
| V | 3.43 | | | | | |

STYLES ON PAGE 2

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| PIN 1. 2. | COLLECTOR EMITTER BASE | PIN 1 | SOURCE | PIN 1. | GATE SOURCE DRAIN | PIN 1. | EMITTER COLLECTOR/ANODE CATHODE | PIN 1. | MT 1 |
| | V _{CC} GROUND 2 OUTPUT | STYLE 27: PIN 1. 2. 3. | MT SUBSTRATE MT | STYLE 28: PIN 1. 2. 3. | CATHODE ANODE GATE | STYLE 29: PIN 1. 2. 3. | NOT CONNECTED ANODE CATHODE | STYLE 30: PIN 1. 2. 3. | DRAIN GATE SOURCE |
| 2. | GATE DRAIN SOURCE | 2. | COLLECTOR | STYLE 33: PIN 1. 2. 3. | INPUT | 2. | INPUT GROUND LOGIC | STYLE 35: PIN 1. 2. 3. | GATE |

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